

1N51
GOLD BONDED GERMANIUM DIODE

FEATURES

Low forward voltage drop—low power consumption
 Thirty years of proven reliability—one million hours mean time between failures (MTBF)
 Very low noise level
 Metallurgically bonded

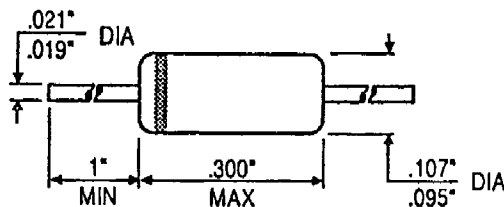
ABSOLUTE MAXIMUM RATINGS (at 25 °C, unless otherwise specified)

Peak Inverse Voltage	50 Volts
Peak Forward Current	500 mA
Operating Temperature Range	- 65 °C to 85 °C
Average Power Dissipation	80 mW

ELECTRICAL CHARACTERISTICS

	Symbol	Conditions	Min	Max	Unit	T °C
Peak Inverse Voltage	PIV	1 mA	50		V	25 °C
Reverse Current	I _r	50 V		1600	μA	25 °C
Forward Voltage	V _f	2.5 mA		1	V	25 °C

MECHANICAL



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